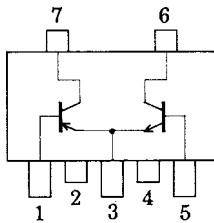


**SANYO****FP212**

PNP/NPN Epitaxial Planar Silicon Transistors

**High-Voltage Driver Applications****Features**

- Composite type with a PNP transistor and an NPN transistor, in one package, facilitating high-density mounting.
- The FP212 is composed of 2 chips, one being equivalent to the 2SA1370 and the other the 2SC3467, placed in one package.

**Electrical Connection**

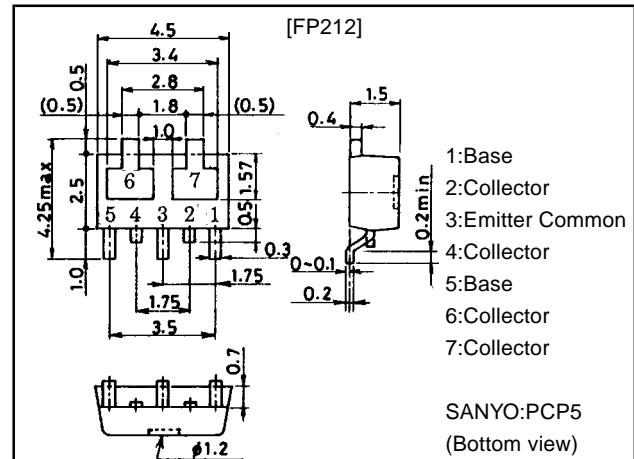
- 1:Base  
2:Collector  
3:Emitter Common  
4:Collector  
5:Base  
6:Collector  
7:Collector

(Top view)

**Package Dimensions**

unit:mm

2097A

**Specifications****Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CB0}$		(-)200	V
Collector-to-Emitter Voltage	$V_{CEO}$		(-)200	V
Emitter-to-Base Voltage	$V_{EBO}$		(-)5	V
Collector Current	$I_C$		(-)100	mA
Collector Current (Pulse)	$I_{CP}$		(-)200	mA
Base Current	$I_B$		(-)10	mA
Collector Dissipation	$P_C$	Mounted on ceramic board (250mm $\times$ 0.8mm) 1 unit	0.75	W
Total Power Dissipation	$P_T$	Mounted on ceramic board (250mm $\times$ 0.8mm)	1.0	W
Junction Temperature	$T_J$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

**Electrical Characteristics at Ta=25°C**

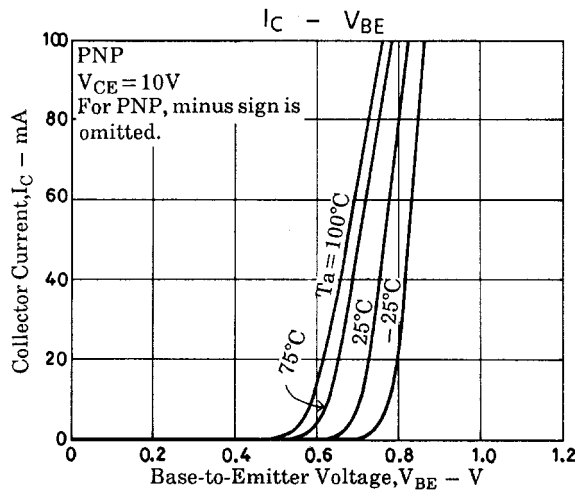
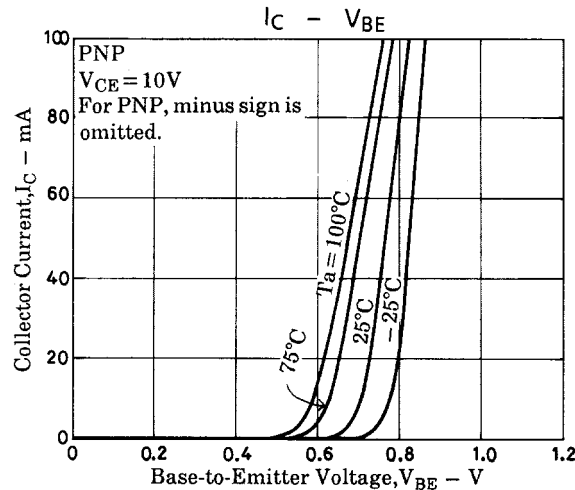
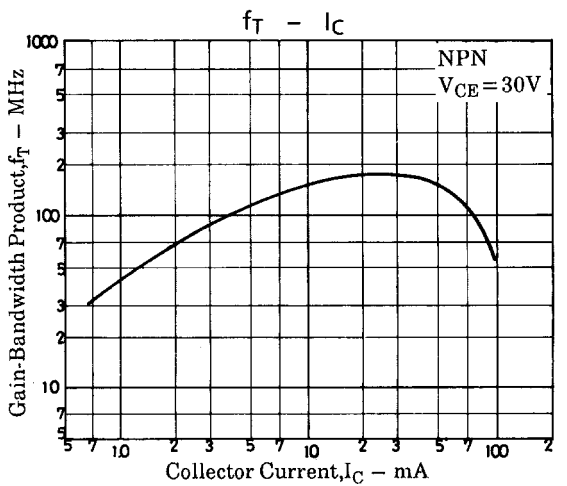
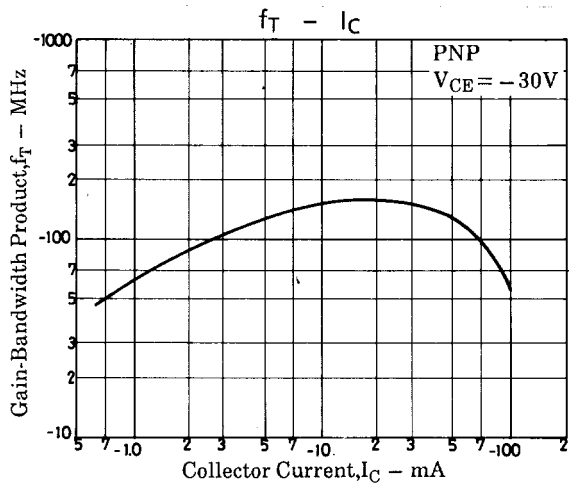
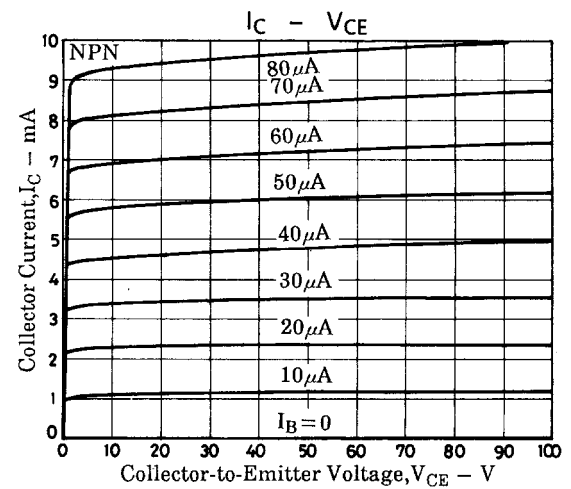
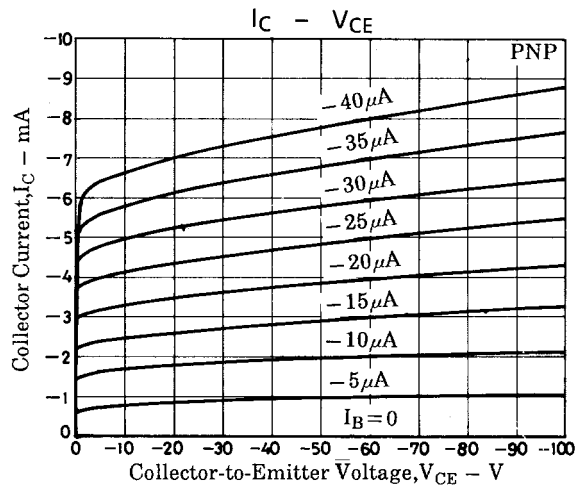
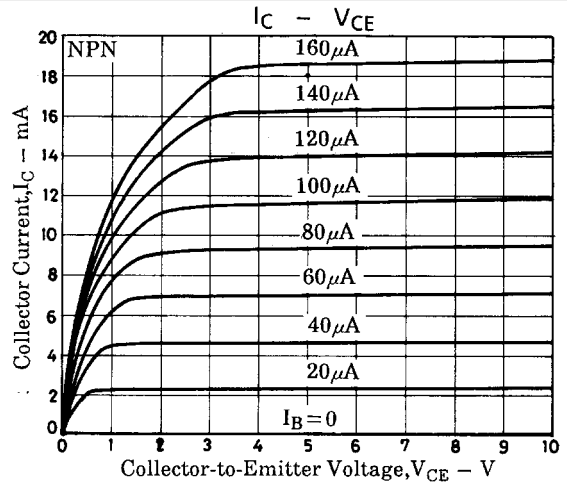
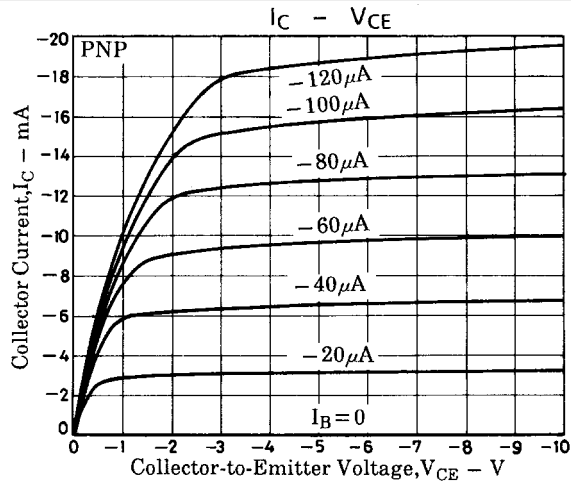
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)150V, I_E = 0$			(-)100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(-)100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = (-)10V, I_C = (-)10mA$	60		200	
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)30V, I_C = (-)10mA$		150		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = (-)30V, f = 1MHz$		(2.6) 1.7		pF
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = (-)30V, f = 1MHz$		(1.7) 1.2		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)200			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)200			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

Marking:212

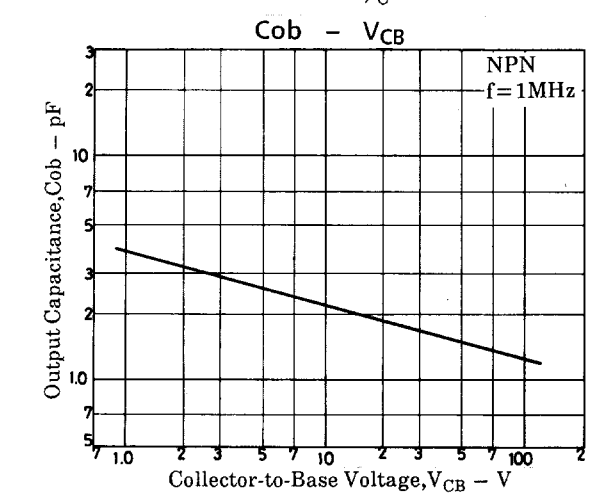
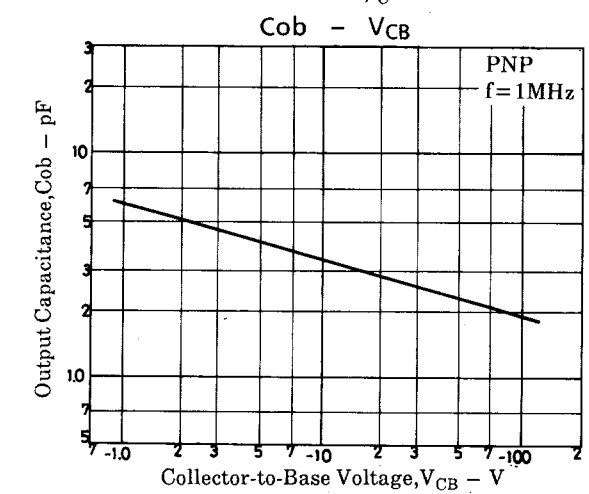
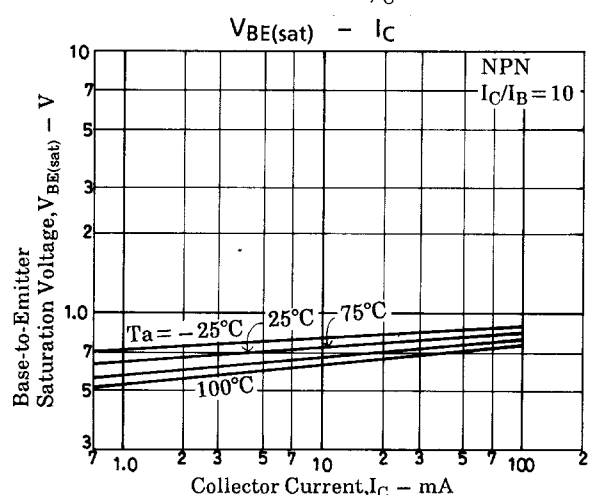
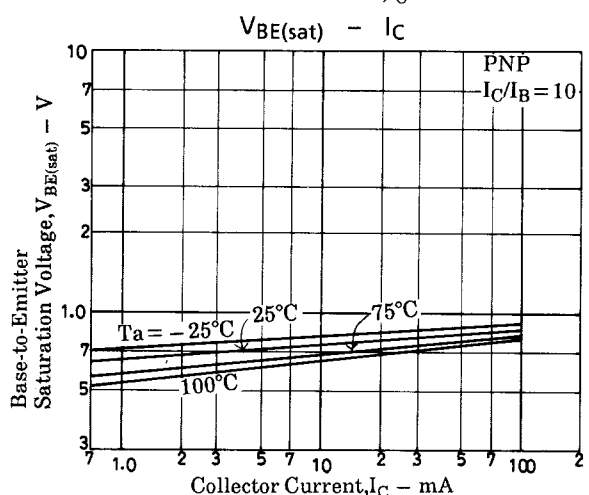
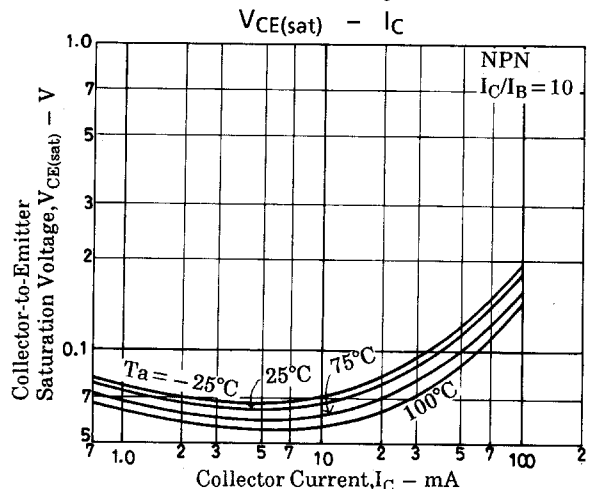
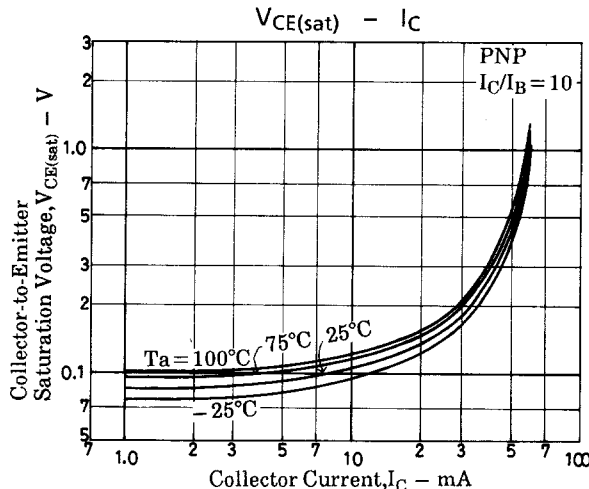
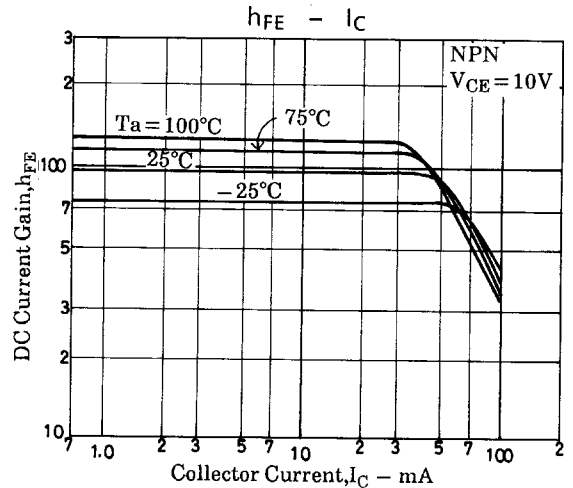
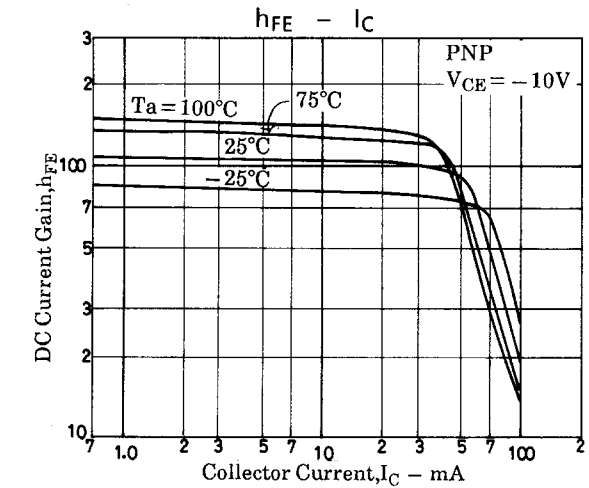
**SANYO Electric Co.,Ltd. Semiconductor Business Headquarters**

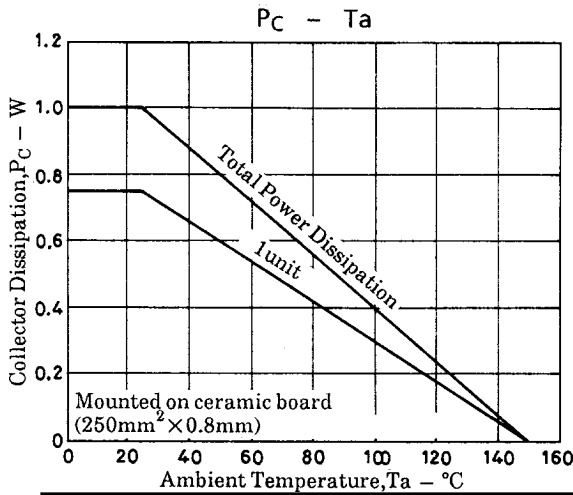
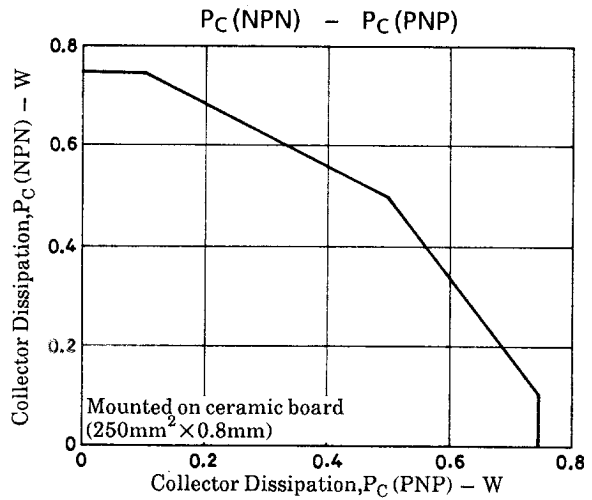
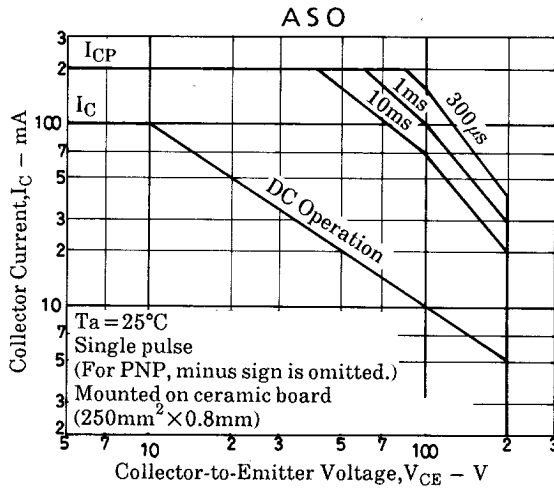
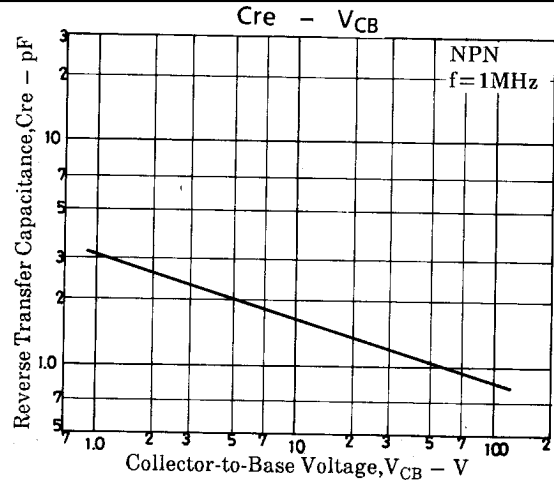
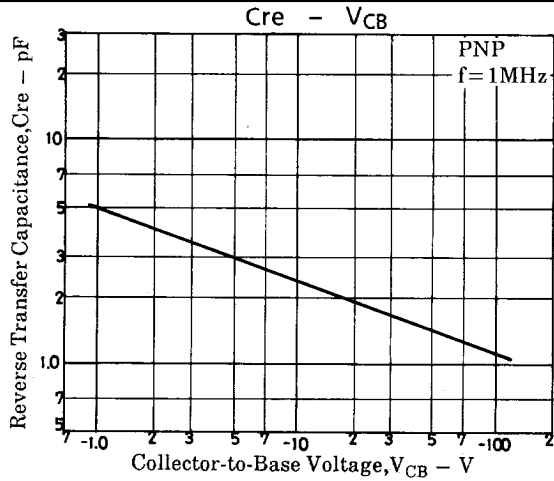
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# FP212



# FP212





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